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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	150
Number of Gates	36000
Voltage - Supply	3V ~ 3.6V, 4.5V ~ 5.5V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	176-LQFP
Supplier Device Package	176-TQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a42mx24-1tq176i

3.3.7 Low Power Mode

42MX devices have been designed with a Low Power Mode. This feature, activated with setting the special LP pin to HIGH for a period longer than 800 ns, is particularly useful for battery-operated systems where battery life is a primary concern. In this mode, the core of the device is turned off and the device consumes minimal power with low standby current. In addition, all input buffers are turned off, and all outputs and bidirectional buffers are tristated. Since the core of the device is turned off, the states of the registers are lost. The device must be re-initialized when exiting Low Power Mode. I/Os can be driven during LP mode, and clock pins should be driven HIGH or LOW and should not float to avoid drawing current. To exit LP mode, the LP pin must be pulled LOW for over 200 µs to allow for charge pumps to power up, and device initialization will begin.

3.4 Power Dissipation

The general power consumption of MX devices is made up of static and dynamic power and can be expressed with the following equation.

3.4.1 General Power Equation

$$P = [ICCstandby + ICCactive]*VCCI + IOL*VOL*N + IOH*(VCCI - VOH)*M$$

EQ 1

where:

- ICCstandby is the current flowing when no inputs or outputs are changing.
- ICCactive is the current flowing due to CMOS switching.
- IOL, IOH are TTL sink/source currents.
- VOL, VOH are TTL level output voltages.
- N equals the number of outputs driving TTL loads to VOL.
- M equals the number of outputs driving TTL loads to VOH.

Accurate values for N and M are difficult to determine because they depend on the family type, on design details, and on the system I/O. The power can be divided into two components: static and active.

3.4.2 Static Power Component

The static power due to standby current is typically a small component of the overall power consumption. Standby power is calculated for commercial, worst-case conditions. The static power dissipation by TTL loads depends on the number of outputs driving, and on the DC load current. For instance, a 32-bit bus sinking 4mA at 0.33V will generate 42mW with all outputs driving LOW, and 140mW with all outputs driving HIGH. The actual dissipation will average somewhere in between, as I/Os switch states with time.

3.4.3 Active Power Component

Power dissipation in CMOS devices is usually dominated by the dynamic power dissipation. Dynamic power consumption is frequency-dependent and is a function of the logic and the external I/O. Active power dissipation results from charging internal chip capacitances of the interconnect, unprogrammed antifuses, module inputs, and module outputs, plus external capacitances due to PC board traces and load device inputs. An additional component of the active power dissipation is the totem pole current in the CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent active power dissipation.

The power dissipated by a CMOS circuit can be expressed by the equation:

$$Power(\mu W) = C_{EQ} * VCCA2 * F(1)$$

EQ 2

where:

- C_{EQ} = Equivalent capacitance expressed in picofarads (pF)

- VCCA = Power supply in volts (V)
- F = Switching frequency in megahertz (MHz)

3.4.4 Equivalent Capacitance

Equivalent capacitance is calculated by measuring ICCactive at a specified frequency and voltage for each circuit component of interest. Measurements have been made over a range of frequencies at a fixed value of VCC. Equivalent capacitance is frequency-independent, so the results can be used over a wide range of operating conditions. Equivalent capacitance values are shown below.

3.4.5 C_{EQ} Values for Microsemi MX FPGAs

Modules (C_{EQM})3.5

Input Buffers (C_{EQI})6.9

Output Buffers (C_{EQO})18.2

Routed Array Clock Buffer Loads (C_{EQCR})1.4

To calculate the active power dissipated from the complete design, the switching frequency of each part of the logic must be known. The equation below shows a piece-wise linear summation over all components.

$$\text{Power} = VCCA^2 * [(m \times C_{EQM} * f_m)_{modules} + (n * C_{EQI} * f_n)_{inputs} + (p * (C_{EQO} + C_L) * f_p)_{outputs} +$$
$$0.5 * (q_1 * C_{EQCR} * f_{q1})_{routed\_Clk1} + (r_1 * f_{q1})_{routed\_Clk1} +$$
$$0.5 * (q_2 * C_{EQCR} * f_{q2})_{routed\_Clk2} + (r_2 * f_{q2})_{routed\_Clk2} (2)]$$

EQ 3

where:

m = Number of logic modules switching at frequency f_m

n = Number of input buffers switching at frequency f_n

p = Number of output buffers switching at frequency f_p

q_1 = Number of clock loads on the first routed array clock

q_2 = Number of clock loads on the second routed array clock

r_1 = Fixed capacitance due to first routed array clock

r_2 = Fixed capacitance due to second routed array clock

C_{EQM} = Equivalent capacitance of logic modules in pF

C_{EQI} = Equivalent capacitance of input buffers in pF

C_{EQO} = Equivalent capacitance of output buffers in pF

C_{EQCR} = Equivalent capacitance of routed array clock in pF

C_L = Output load capacitance in pF

f_m = Average logic module switching rate in MHz

f_n = Average input buffer switching rate in MHz

f_p = Average output buffer switching rate in MHz

f_{q1} = Average first routed array clock rate in MHz

Additionally, the back-annotation flow is compatible with all the major simulators and the simulation results can be cross-probed with Silicon Explorer II, Microsemi's integrated verification and logic analysis tool. Another tool included in the Libero software is the SmartGen macro builder, which easily creates popular and commonly used logic functions for implementation into your schematic or HDL design.

Microsemi's Libero software is compatible with the most popular FPGA design entry and verification tools from companies such as Mentor Graphics, Synopsys, and Cadence design systems.

See the Libero IDE web content at www.microsemi.com/soc/products/software/libero/default.aspx for further information on licensing and current operating system support.

3.6 Related Documents

The following sections give the list of related documents which can be refered for this datasheet.

3.6.1 Application Notes

- *AC278: BSDL Files Format Description*
- *AC225: Programming Antifuse Devices*
- *AC168: Implementation of Security in Microsemi Antifuse FPGAs*

3.6.2 User Guides and Manuals

- *Antifuse Macro Library Guide*
- *Silicon Sculptor Programmers User Guide*

3.6.3 Miscellaneous

Libero IDE Flow Diagram

3.7 5.0 V Operating Conditions

The following tables show 5.0 V operating conditions.

Table 12 • **Absolute Maximum Ratings for 40MX Devices***

Symbol	Parameter	Limits	Units
VCC	DC Supply Voltage	–0.5 to +7.0	V
VI	Input Voltage	–0.5 to VCC+0.5	V
VO	Output Voltage	–0.5 to VCC+0.5	V
t_{STG}	Storage Temperature	–65 to +150	°C

Note: *Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Devices should not be operated outside the recommended operating conditions.

Table 13 • **Absolute Maximum Ratings for 42MX Devices***

Symbol	Parameter	Limits	Units
VCCI	DC Supply Voltage for I/Os	–0.5 to +7.0	V
VCCA	DC Supply Voltage for Array	–0.5 to +7.0	V
VI	Input Voltage	–0.5 to VCCI+0.5	V
VO	Output Voltage	–0.5 to VCCI+0.5	V
t_{STG}	Storage Temperature	–65 to +150	°C

Note: *Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Devices should not be operated outside the recommended operating conditions.

Table 14 • **Recommended Operating Conditions**

Parameter	Commercial	Industrial	Military	Units
Temperature Range*	0 to +70	–40 to +85	–55 to +125	°C
VCC (40MX)	4.75 to 5.25	4.5 to 5.5	4.5 to 5.5	V
VCCA (42MX)	4.75 to 5.25	4.5 to 5.5	4.5 to 5.5	V
VCCI (42MX)	4.75 to 5.25	4.5 to 5.5	4.5 to 5.5	V

Note: * Ambient temperature (T_A) is used for commercial and industrial grades; case temperature (T_C) is used for military grades.

3.7.1 5 V TTL Electrical Specifications

The following tables show 5 V TTL electrical specifications.

Table 15 • **5V TTL Electrical Specifications**

		Commercial		Commercial -F		Industrial		Military		
Symbol	**Parameter**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Units**
VOH[1]	IOH = –10 mA	2.4		2.4						V
	IOH = –4 mA					3.7		3.7		V
VOL[1]	IOL = 10 mA		0.5		0.5					V
	IOL = 6 mA						0.4		0.4	V
VIL		–0.3	0.8	–0.3	0.8	–0.3	0.8	–0.3	0.8	V
VIH (40MX)		2.0	VCC + 0.3	2.0	VCC + 0.3	2.0	VCC + 0.3	2.0	VCC + 0.3	V
VIH (42MX)[2]		2.0	VCCI + 0.3	2.0	VCCI + 0.3	2.0	VCCI + 0.3	2.0	VCCI + 0.3	V
IIL	VIN = 0.5 V		–10		–10		–10		–10	µA
IIH	VIN = 2.7 V		–10		–10		–10		–10	µA
Input Transition Time, T_R and T_F			500		500		500		500	ns
C_{IO} I/O Capacitance			10		10		10		10	pF
Standby Current, ICC[3]	A40MX02, A40MX04		3		25		10		25	mA
	A42MX09		5		25		25		25	mA
	A42MX16		6		25		25		25	mA
	A42MX24, A42MX36		20		25		25		25	mA
Low power mode Standby Current	42MX devices only		0.5		ICC – 5.0		ICC – 5.0		ICC – 5.0	mA
IIO, I/O source sink current	Can be derived from the *IBIS model* (http://www.microsemi.com/soc/techdocs/models/ibis.html)									

1. Only one output tested at a time. VCC/VCCI = min
2. VIH(Min) is 2.4V for A42MX36 family. This applies only to VCCI of 5V and is not applicable to VCCI of 3.3V

A sample calculation of the absolute maximum power dissipation allowed for a TQ176 package at commercial temperature and still air is given in the following equation

$$\text{MaximumPowerAllowed} = \frac{\text{Max} \cdot \text{junction temp} \cdot (°\text{C}) - \text{Max} \cdot \text{ambient temp} \cdot (°\text{C})}{\theta_{ja}(°(\text{C}/\text{W}))} = \frac{150°\text{C} - 70°\text{C}}{(28°\text{C})/\text{W}} = 2.86\text{W}$$

EQ 5

The maximum power dissipation for military-grade devices is a function of θ_{jc}. A sample calculation of the absolute maximum power dissipation allowed for CQFP 208-pin package at military temperature and still air is given in the following equation

$$\text{MaximumPowerAllowed} = \frac{\text{Max} \cdot \text{junction temp} \cdot (°\text{C}) - \text{Max} \cdot \text{ambient temp} \cdot (°\text{C})}{\theta_{jc}(°(\text{C}/\text{W}))} = \frac{150°\text{C} - 125°\text{C}}{(6.3°\text{C})/\text{W}} = 3.97\text{W}$$

EQ 6

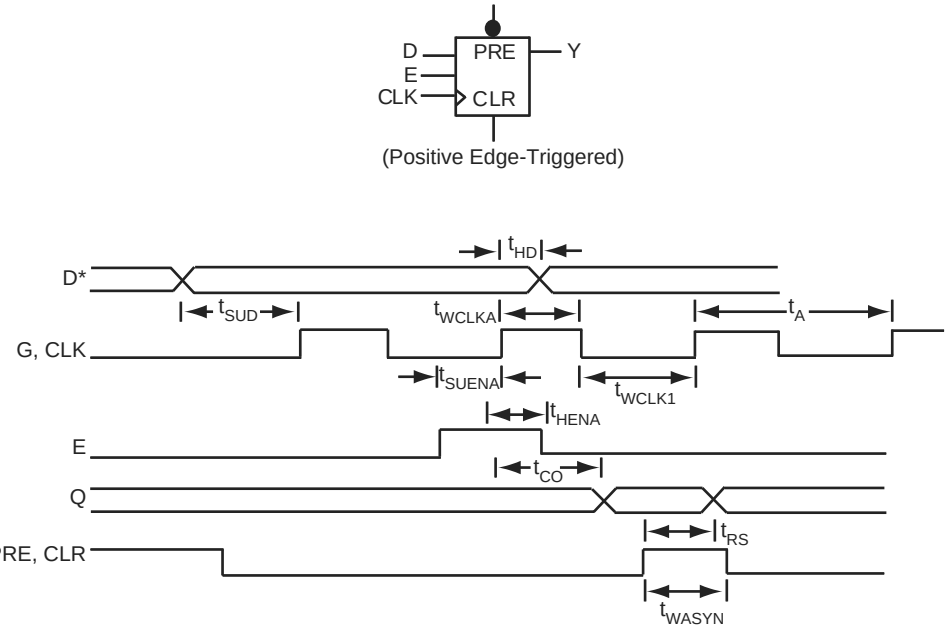
Table 27 • **Package Thermal Characteristics**

			θ_{ja}			
Plastic Packages	**Pin Count**	θ_{jc}	**Still Air**	**1.0 m/s 200 ft/min.**	**2.5 m/s 500 ft/min.**	**Units**
Plastic Quad Flat Pack	100	12.0	27.8	23.4	21.2	°C/W
Plastic Quad Flat Pack	144	10.0	26.2	22.8	21.1	°C/W
Plastic Quad Flat Pack	160	10.0	26.2	22.8	21.1	°C/W
Plastic Quad Flat Pack	208	8.0	26.1	22.5	20.8	°C/W
Plastic Quad Flat Pack	240	8.5	25.6	22.3	20.8	°C/W
Plastic Leaded Chip Carrier	44	16.0	20.0	24.5	22.0	°C/W
Plastic Leaded Chip Carrier	68	13.0	25.0	21.0	19.4	°C/W
Plastic Leaded Chip Carrier	84	12.0	22.5	18.9	17.6	°C/W
Thin Plastic Quad Flat Pack	176	11.0	24.7	19.9	18.0	°C/W
Very Thin Plastic Quad Flat Pack	80	12.0	38.2	31.9	29.4	°C/W
Very Thin Plastic Quad Flat Pack	100	10.0	35.3	29.4	27.1	°C/W
Plastic Ball Grid Array	272	3.0	18.3	14.9	13.9	°C/W
Ceramic Packages						
Ceramic Pin Grid Array	132	4.8	25.0	20.6	18.7	°C/W
Ceramic Quad Flat Pack	208	2.0	22.0	19.8	18.0	°C/W
Ceramic Quad Flat Pack	256	2.0	20.0	16.5	15.0	°C/W

3.10.2 Sequential Module Timing Characteristics

The following figure shows sequential module timing characteristics.

Figure 25 • **Flip-Flops and Latches**



Note: *D represents all data functions involving A, B, and S for multiplexed flip-flops.

3.10.3 Sequential Timing Characteristics

The following figures show sequential timing characteristics.

Figure 26 • **Input Buffer Latches**

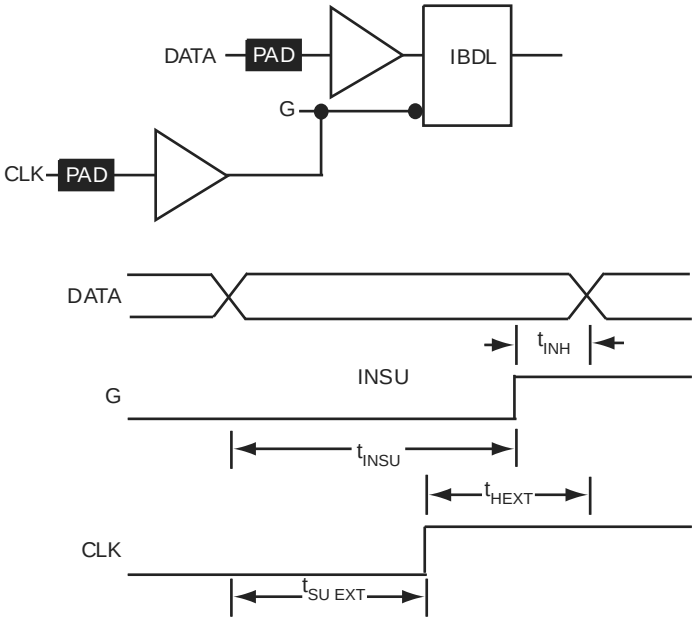
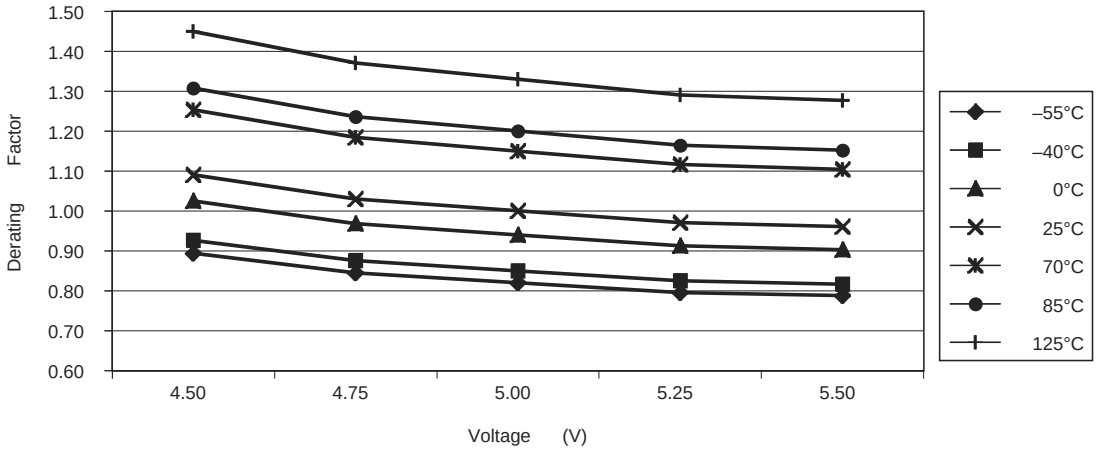


Figure 35 • **40MX Junction Temperature and Voltage Derating Curves (Normalized to TJ = 25°C, VCC = 5.0 V)**

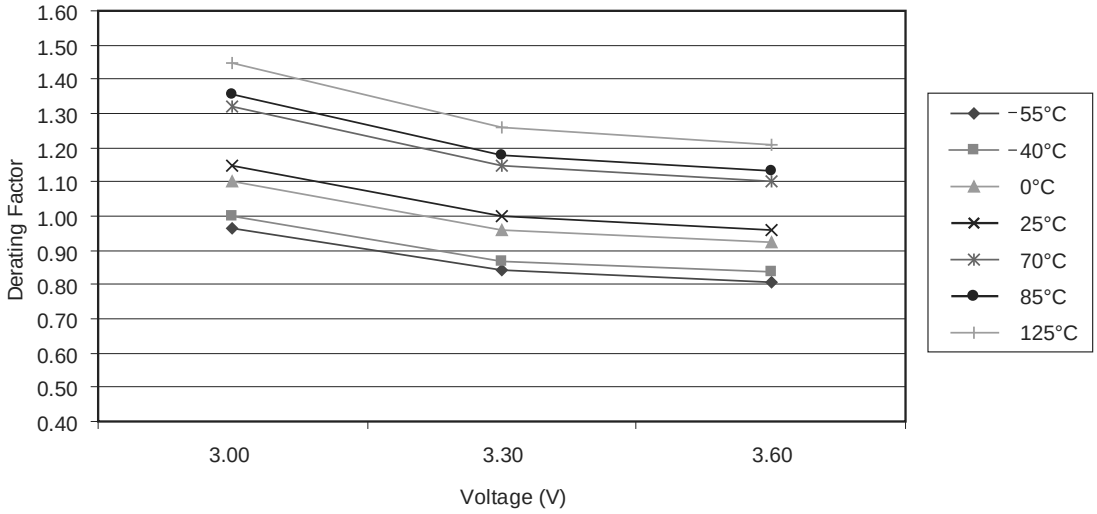


Note: This derating factor applies to all routing and propagation delays

Table 30 • **42MX Temperature and Voltage Derating Factors(Normalized to TJ = 25°C, VCCA = 3.3 V)**

	Temperature						
42MX Voltage	**–55°C**	**–40°C**	**0°C**	**25°C**	**70°C**	**85°C**	**125°C**
3.00	0.97	1.00	1.10	1.15	1.32	1.36	1.45
3.30	0.84	0.87	0.96	1.00	1.15	1.18	1.26
3.60	0.81	0.84	0.92	0.96	1.10	1.13	1.21

Figure 36 • **42MX Junction Temperature and Voltage Derating Curves (Normalized to TJ = 25°C, VCCA = 3.3 V)**



Note: This derating factor applies to all routing and propagation delays

Table 31 • **40MX Temperature and Voltage Derating Factors (Normalized to TJ = 25°C, VCC = 3.3 V)**

	Temperature						
40MX Voltage	**–55°C**	**–40°C**	**0°C**	**25°C**	**70°C**	**85°C**	**125°C**
3.00	1.08	1.12	1.21	1.26	1.50	1.64	2.00
3.30	0.86	0.89	0.96	1.00	1.19	1.30	1.59

Table 43 • **A42MX24 Timing Characteristics (Nominal 3.3 V Operation) *(continued)*(Worst-Case Commercial Conditions, VCCA = 3.0 V, T_J = 70°C)**

Parameter / Description			–3 Speed		–2 Speed		–1 Speed		Std Speed		–F Speed		Units
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Input Module Predicted Routing Delays[2]													
t_{IRD1}	FO = 1 Routing Delay			2.6		2.9		3.2		3.8		5.3	ns
t_{IRD2}	FO = 2 Routing Delay			2.9		3.2		3.6		4.3		6.0	ns
t_{IRD3}	FO = 3 Routing Delay			3.2		3.6		4.0		4.8		6.6	ns
t_{IRD4}	FO = 4 Routing Delay			3.5		3.9		4.4		5.2		7.3	ns
t_{IRD8}	FO = 8 Routing Delay			4.8		5.3		6.1		7.1		10.0	ns
Global Clock Network													
t_{CKH}	Input LOW to HIGH	FO = 32		4.4		4.8		5.5		6.5		9.1	ns
		FO = 486		4.8		5.3		6.0		7.1		10.0	ns
t_{CKL}	Input HIGH to LOW	FO = 32		5.1		5.7		6.4		7.6		10.6	ns
		FO = 486		6.0		6.6		7.5		8.8		12.4	ns
t_{PWH}	Minimum Pulse Width HIGH	FO = 32	3.0		3.3		3.8		4.5		6.3		ns
		FO = 486	3.3		3.7		4.2		4.9		6.9		ns
t_{PWL}	Minimum Pulse Width LOW	FO = 32	3.0		3.4		3.8		4.5		6.3		ns
		FO = 486	3.3		3.7		4.2		4.9		6.9		ns
t_{CKSW}	Maximum Skew	FO = 32		0.8		0.8		1.0		1.1		1.6	ns
		FO = 486		0.8		0.8		1.0		1.1		1.6	ns
t_{SUEXT}	Input Latch External Set-Up	FO = 32	0.0		0.0		0.0		0.0		0.0		ns
		FO = 486	0.0		0.0		0.0		0.0		0.0		ns
TTL Output Module Timing[5]													
t_{DLH}	Data-to-Pad HIGH			3.4		3.8		4.3		5.0		7.1	ns
t_{DHL}	Data-to-Pad LOW			4.0		4.4		5.0		5.9		8.3	ns
t_{ENZH}	Enable Pad Z to HIGH			3.6		4.0		4.5		5.3		7.4	ns
t_{ENZL}	Enable Pad Z to LOW			3.9		4.4		5.0		5.8		8.2	ns
t_{ENHZ}	Enable Pad HIGH to Z			7.2		8.0		9.1		10.7		14.9	ns
t_{ENLZ}	Enable Pad LOW to Z			6.7		7.5		8.5		9.9		13.9	ns
t_{GLH}	G-to-Pad HIGH			4.8		5.3		6.0		7.2		10.0	ns
t_{GHL}	G-to-Pad LOW			4.8		5.3		6.0		7.2		10.0	ns
t_{LSU}	I/O Latch Output Set-Up		0.7		0.7		0.8		1.0		1.4		ns

Table 44 • **A42MX36 Timing Characteristics (Nominal 5.0 V Operation)(Worst-Case Commercial Conditions, VCCA = 4.75 V, T_J = 70°C)**

Parameter / Description			–3 Speed		–2 Speed		–1 Speed		Std Speed		–F Speed		Units
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Asynchronous SRAM Operations													
t_{RPD}	Asynchronous Access Time			8.1		9.0		10.2		12.0		16.8	ns
t_{RDADV}	Read Address Valid		8.8		9.8		11.1		13.0		18.2		ns
t_{ADSU}	Address/Data Set-Up Time		1.6		1.8		2.0		2.4		3.4		ns
t_{ADH}	Address/Data Hold Time		0.0		0.0		0.0		0.0		0.0		ns
t_{RENSUA}	Read Enable Set-Up to Address Valid		0.6		0.7		0.8		0.9		1.3		ns
t_{RENHA}	Read Enable Hold		3.4		3.8		4.3		5.0		7.0		ns
t_{WENSU}	Write Enable Set-Up		2.7		3.0		3.4		4.0		5.6		ns
t_{WENH}	Write Enable Hold		0.0		0.0		0.0		0.0		0.0		ns
t_{DOH}	Data Out Hold Time			1.2		1.3		1.5		1.8		2.5	ns
Input Module Propagation Delays													
t_{INPY}	Input Data Pad-to-Y			1.0		1.1		1.3		1.5		2.1	ns
t_{INGO}	Input Latch Gate-to-Output			1.4		1.6		1.8		2.1		2.9	ns
t_{INH}	Input Latch Hold		0.0		0.0		0.0		0.0		0.0		ns
t_{INSU}	Input Latch Set-Up		0.5		0.5		0.6		0.7		1.0		ns
t_{ILA}	Latch Active Pulse Width		4.7		5.2		5.9		6.9		9.7		ns
Input Module Predicted Routing Delays[2]													
t_{IRD1}	FO = 1 Routing Delay			2.0		2.2		2.5		2.9		4.1	ns
t_{IRD2}	FO = 2 Routing Delay			2.3		2.6		2.9		3.4		4.8	ns
t_{IRD3}	FO = 3 Routing Delay			2.6		2.9		3.3		3.9		5.5	ns
t_{IRD4}	FO = 4 Routing Delay			3.0		3.3		3.8		4.4		6.2	ns
t_{IRD8}	FO = 8 Routing Delay			4.3		4.8		5.5		6.4		9.0	ns
Global Clock Network													
t_{CKH}	Input LOW to HIGH	FO = 32		2.7		3.0		3.4		4.0		5.6	ns
		FO = 635		3.0		3.3		3.8		4.4		6.2	ns
t_{CKL}	Input HIGH to LOW	FO = 32		3.8		4.2		4.8		5.6		7.8	ns
		FO = 635		4.9		5.4		6.1		7.2		10.1	ns
t_{PWH}	Minimum Pulse Width HIGH	FO = 32	1.8		2.0		2.2		2.6		3.6		ns
		FO = 635	2.0		2.2		2.5		2.9		4.1		ns
t_{PWL}	Minimum Pulse Width LOW	FO = 32	1.8		2.0		2.2		2.6		3.6		ns
		FO = 635	2.0		2.2		2.5		2.9		4.1		ns
t_{CKSW}	Maximum Skew	FO = 32		0.8		0.8		0.9		1.0		1.4	ns
		FO = 635		0.8		0.8		0.9		1.0		1.4	ns

Table 45 • **A42MX36 Timing Characteristics (Nominal 3.3 V Operation) *(continued)*(Worst-Case Commercial Conditions, VCCA = 3.0 V, T_J = 70°C)**

		–3 Speed		–2 Speed		–1 Speed		Std Speed		–F Speed		
Parameter / Description		**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Units**
Synchronous SRAM Operations (continued)												
t_{ADH}	Address/Data Hold Time	0.0		0.0		0.0		0.0		0.0		ns
t_{RENSU}	Read Enable Set-Up	0.9		1.0		1.1		1.3		1.8		ns
t_{RENH}	Read Enable Hold	4.8		5.3		6.0		7.0		9.8		ns
t_{WENSU}	Write Enable Set-Up	3.8		4.2		4.8		5.6		7.8		ns
t_{WENH}	Write Enable Hold	0.0		0.0		0.0		0.0		0.0		ns
t_{BENS}	Block Enable Set-Up	3.9		4.3		4.9		5.7		8.0		ns
t_{BENH}	Block Enable Hold	0.0		0.0		0.0		0.0		0.0		ns
Asynchronous SRAM Operations												
t_{RPD}	Asynchronous Access Time		11.3		12.6		14.3		16.8		23.5	ns
t_{RDADV}	Read Address Valid	12.3		13.7		15.5		18.2		25.5		ns
t_{ADSU}	Address/Data Set-Up Time	2.3		2.5		2.8		3.4		4.8		ns
t_{ADH}	Address/Data Hold Time	0.0		0.0		0.0		0.0		0.0		ns
t_{RENSUA}	Read Enable Set-Up to Address Valid	0.9		1.0		1.1		1.3		1.8		ns
t_{RENHA}	Read Enable Hold	4.8		5.3		6.0		7.0		9.8		ns
t_{WENSU}	Write Enable Set-Up	3.8		4.2		4.8		5.6		7.8		ns
t_{WENH}	Write Enable Hold	0.0		0.0		0.0		0.0		0.0		ns
t_{DOH}	Data Out Hold Time		1.8		2.0		2.1		2.5		3.5	ns
Input Module Propagation Delays												
t_{INPY}	Input Data Pad-to-Y		1.4		1.6		1.8		2.1		3.0	ns
t_{INGO}	Input Latch Gate-to-Output		2.0		2.2		2.5		2.9		4.1	ns
t_{INH}	Input Latch Hold	0.0		0.0		0.0		0.0		0.0		ns
t_{INSU}	Input Latch Set-Up	0.7		0.7		0.8		1.0		1.4		ns
t_{ILA}	Latch Active Pulse Width	6.5		7.3		8.2		9.7		13.5		ns

Table 49 • **PL84**

PL84				
Pin Number	**A40MX04 Function**	**A42MX09 Function**	**A42MX16 Function**	**A42MX24 Function**
84	I/O	VCCA	VCCA	VCCA

Figure 41 • **PQ100**

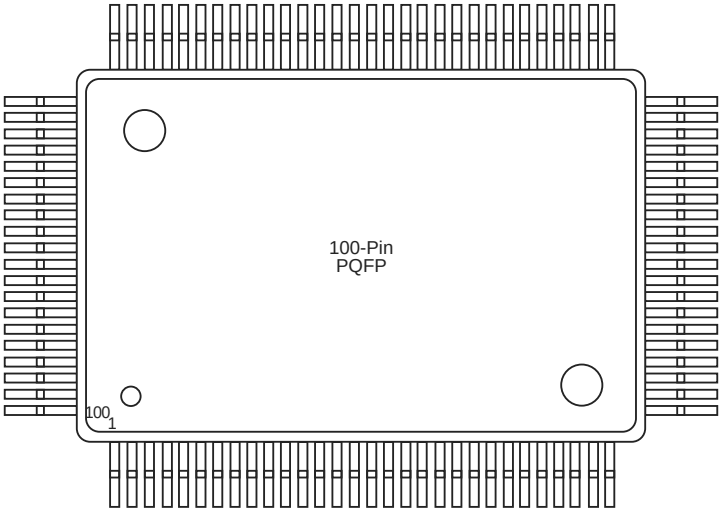


Table 50 • **PQ 100**

PQ100				
Pin Number	**A40MX02 Function**	**A40MX04 Function**	**A42MX09 Function**	**A42MX16 Function**
1	NC	NC	I/O	I/O
2	NC	NC	DCLK, I/O	DCLK, I/O
3	NC	NC	I/O	I/O
4	NC	NC	MODE	MODE
5	NC	NC	I/O	I/O
6	PRB, I/O	PRB, I/O	I/O	I/O
7	I/O	I/O	I/O	I/O
8	I/O	I/O	I/O	I/O
9	I/O	I/O	GND	GND
10	I/O	I/O	I/O	I/O
11	I/O	I/O	I/O	I/O
12	I/O	I/O	I/O	I/O
13	GND	GND	I/O	I/O
14	I/O	I/O	I/O	I/O
15	I/O	I/O	I/O	I/O
16	I/O	I/O	VCCA	VCCA
17	I/O	I/O	VCCI	VCCA
18	I/O	I/O	I/O	I/O

Figure 42 • **PQ144**

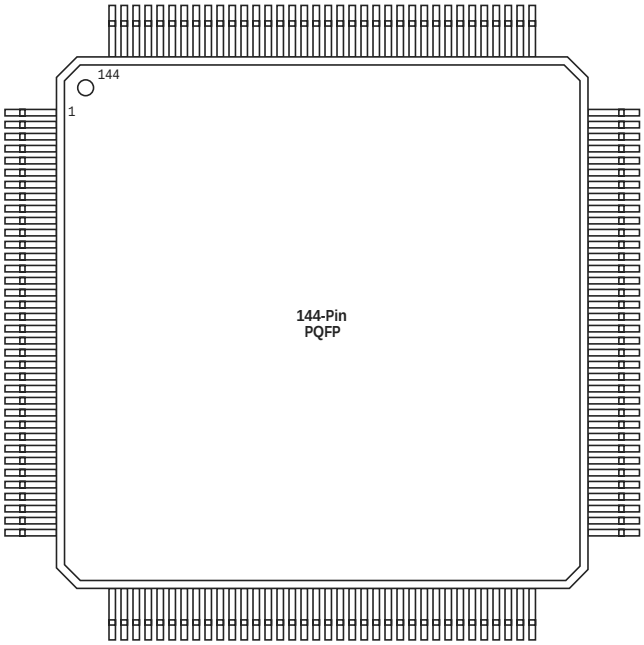


Table 51 • **PQ144**

PQ144	
Pin Number	**A42MX09 Function**
1	I/O
2	MODE
3	I/O
4	I/O
5	I/O

Table 51 • **PQ144**

PQ144	
Pin Number	**A42MX09 Function**
6	I/O
7	I/O
8	I/O
9	GNDQ
10	GNDI
11	NC
12	I/O
13	I/O
14	I/O
15	I/O
16	I/O
17	I/O
18	VSV
19	VCC
20	VCCI
21	NC
22	I/O
23	I/O
24	I/O
25	I/O
26	I/O
27	I/O
28	GND
29	GNDI
30	NC
31	I/O
32	I/O
33	I/O
34	I/O
35	I/O
36	I/O
37	BININ
38	BINOUT
39	I/O
40	I/O
41	I/O
42	I/O

Table 51 • **PQ144**

PQ144	
Pin Number	**A42MX09 Function**
117	GNDI
118	NC
119	I/O
120	I/O
121	I/O
122	I/O
123	PROBA
124	I/O
125	CLKA
126	VCC
127	VCCI
128	NC
129	I/O
130	CLKB
131	I/O
132	PROBB
133	I/O
134	I/O
135	I/O
136	GND
137	GNDI
138	NC
139	I/O
140	I/O
141	I/O
142	I/O
143	I/O
144	DCLK

Table 58 • **CQ208**

CQ208	
Pin Number	**A42MX36 Function**
148	I/O
149	I/O
150	GND
151	I/O
152	I/O
153	I/O
154	I/O
155	I/O
156	I/O
157	GND
158	I/O
159	SDI, I/O
160	I/O
161	WD, I/O
162	WD, I/O
163	I/O
164	VCCI
165	I/O
166	I/O
167	I/O
168	WD, I/O
169	WD, I/O
170	I/O
171	QCLKD, I/O
172	I/O
173	I/O
174	I/O
175	I/O
176	WD, I/O
177	WD, I/O
178	PRA, I/O
179	I/O
180	CLKA, I/O
181	I/O
182	VCCI
183	VCCA
184	GND

Table 60 • **BG272**

BG272	
Pin Number	**A42MX36 Function**
Y13	I/O
Y14	I/O
Y15	I/O
Y16	I/O
Y17	I/O
Y18	WD, I/O
Y19	GND
Y20	GND

Figure 52 • **PG132**

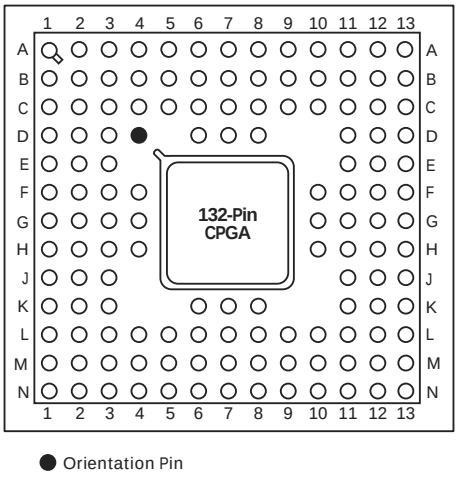


Table 61 • **PG132**

PG132	
Pin Number	**A42MX09 Function**
–	PMPOUT
B2	I/O
A1	MODE
B1	I/O
D3	I/O
C2	I/O
C1	I/O
D2	I/O
D1	I/O
E2	I/O
E1	I/O
F3	I/O

Table 61 • **PG132**

PG132	
Pin Number	**A42MX09 Function**
N10	I/O
M10	I/O
N11	I/O
L10	I/O
M11	I/O
N12	SDO
M12	I/O
L11	I/O
N13	I/O
M13	I/O
K11	I/O
L12	I/O
L13	I/O
K13	I/O
H10	I/O
J12	I/O
J13	I/O
H11	I/O
H12	I/O
H13	VKS
G13	VPP

Figure 53 • **CQ172**

Table 62 • **CQ172**

CQ172	
Pin Number	**A42MX16 Function**
1	MODE
2	I/O
3	I/O
4	I/O
5	I/O
6	I/O
7	GND
8	I/O
9	I/O
10	I/O
11	I/O
12	VCC
13	I/O
14	I/O
15	I/O
16	I/O
17	GND
18	I/O
19	I/O
20	I/O

Table 62 • **CQ172**

138	I/O
139	I/O
140	I/O
141	GND
142	I/O
143	I/O
144	I/O
145	I/O
146	I/O
147	I/O
148	PROBA
149	I/O
150	CLKA
151	VCC
152	GND
153	I/O
154	CLKB
155	I/O
156	PROBB
157	I/O
158	I/O
159	I/O
160	I/O
161	GND
162	I/O
163	I/O
164	I/O
165	I/O
166	VCCI
167	I/O
168	I/O
169	I/O
170	I/O
171	DCLK